

REMARKS

Claims 1-42 are pending with claims 25, 28, 31, 34, 37, and 40 being independent. Claims 1-24 were withdrawn due to a previous restriction requirement and claims 25-30 have been examined. Claims 31-42 are being added by this amendment. No new matter has been added.

Claims 25-27 stand rejected under 35 U.S.C. § 102(e) as being anticipated by Zhang et al. (5,508,209). Applicants respectfully traverse this rejection.

Claim 25 recites a method of manufacturing a semiconductor device that includes, among other features, forming an amorphous semiconductor film over a substrate and irradiating the amorphous semiconductor film with a second harmonic of a continuous wave laser comprising Nd to crystallize the amorphous semiconductor film. Applicants request reconsideration and withdrawal of the rejection because Zhang fails to describe or suggest irradiating the amorphous semiconductor film with a second harmonic of a continuous wave laser comprising Nd to crystallize the amorphous semiconductor film as recited in claim 25. Rather, Zhang describes using an infrared laser light, such as a Nd:YAG laser light and a second harmonic of the infrared laser to irradiate a crystallized semiconductor film. See Zhang, col. 8, lines 24-34, and col. 8, line 62 to col. 9, line 12.

For at least this reason, applicants respectfully request withdrawal of the rejection of claim 25 and its dependent claims 26 and 27.

Claims 25-30 stand rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 17-21, 22-27, 34-43, 48-56, and 61-80 of Kusumoto et al. (6,204,099). A terminal disclaimer is being filed concurrently with this response to obviate the obviousness-type double patenting rejection.

For at least this reason, applicants respectfully request withdrawal of this rejection of claims 25-30.

New claims 31-42 are being added by this amendment. No new matter is being added. Independent claim 31 recites a method for manufacturing a semiconductor device that includes, among other features, forming an amorphous semiconductor film and irradiating the amorphous

semiconductor film with a second harmonic of a laser comprising Nd to crystallize the amorphous semiconductor film. Independent claim 34 recites a method for manufacturing a semiconductor device that includes, among other features, forming an amorphous semiconductor film over a substrate and irradiating the amorphous semiconductor film with a third harmonic of a laser comprising Nd to crystallize the amorphous semiconductor film. Independent claim 37 recites a method of manufacturing a semiconductor device that includes, among other features, forming an amorphous semiconductor film over a substrate, patterning the amorphous semiconductor film into a first shape amorphous semiconductor island, and irradiating the first shape amorphous semiconductor island with a second harmonic of a laser comprising Nd to crystallize the first shape amorphous semiconductor island. Independent claim 40 recites a method of manufacturing a semiconductor device that includes, among other features, forming an amorphous semiconductor film over a substrate, patterning the amorphous semiconductor film into a first shape amorphous semiconductor island, and irradiating the first shape amorphous semiconductor island with a third harmonic of a laser comprising Nd to crystallize the first shape amorphous semiconductor island.

Applicants respectfully request that new claims 31-42 be allowed because the cited prior art fails to describe or suggest these features.

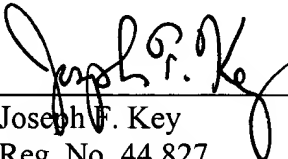
Applicant : Kusumoto et al.
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Enclosed is a \$894.00 check of which \$474.00 is for excess claim fees and \$420.00 is for the Petition for Extension of Time fee. During the prosecution of this application, please apply any deficiencies or credits to deposit account 06-1050.

Respectfully submitted,

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